

650V 75A Trench and Field Stop IGBT

DESCRIPTION :

- High ruggedness performance
- · Easy parallel switching capability
- Trench and field-stop technology.
- · High efficiency for inverters
- RoHS compliant.

TYPICAL APPLICATIONS :

- · Hair removal device
- Flash light

IGBT

MAXIMUM RATINGS (Tvj=25°C unless otherwise specified)

| Characteristic | Condition | Symbol | Value | Unit |
|--|----------------------------------|--------------------|------------|------|
| Collector-Emitter Voltage | | V _{CES} | 650 | V |
| Continuous collector current | Tc=25℃ Tc=100℃ | I _{C nom} | 125 75 | А |
| Pulsed collector current | t _P limited by Tvjmax | I _{CM} | 300 | А |
| Gate emitter voltage | | V _{GE} | ±20 | V |
| Power dissipation | Tc=25℃ Tc=100℃ | P _{tot} | 535 267 | W |
| Temperature under switching conditions | | Tvj op | -40~+175 | °C |
| Storage temperature | | T _{STG} | -55~+150 | °C |

THERMAL CHARACTERISTICS

| Characteristic | Condition | Symbol | Max. | Unit |
|---|-----------|----------------------|------|------|
| IGBT thermal resistance, junction - case | | $R_{th(j-C)}$ | 0.28 | K/W |
| Thermal resistance, junction - ambient | | R _{th(j-A)} | 40 | K/W |



TO-263

ELECTRICAL CHARATERISTICS

| Characteristic | Symbol | Min. | Тур. | Max. | Unit |
|---|---------------------|------|------------|------|------|
| Collector-emitter breakdown voltage VGE=0V, Ic=250uA | BV _{CES} | 650 | | | V |
| Collector-emitter cut-off current VCE=650V, VGE=0V Tvj=25℃ | I _{CES} | | | 50 | uA |
| Gate-emitter leakage current VCE=0V, VGE=20V Tvj=25℃ | I _{GES} | | | 100 | nA |
| Gate-Emitter threshold voltage IC=1.0mA, VGE= VCE Tvj=25°C | $V_{GE(th)}$ | 5.0 | 5.4 | 5.6 | V |
| Collector-Emitter saturation voltage VGE=15V, IC=75A Tvj=25℃ VGE=15V, IC=75A Tvj=175℃ | $V_{CE(SAT)}$ | | 1.8 2.3 | | V |
| Input capacitance f=1MHz, VCE=30 V, VGE=0 V Tvj=25°C | C _{ies} | | 4250 | | pF |
| Output capacitance f=1MHz, VCE=30 V, VGE=0 V Tvj=25℃ | C _{oes} | | 205 | | pF |
| Reverse transfer capacitance f=1MHz, VCE=30 V, VGE=0 V Tvj=25℃ | C _{res} | | 31 | | pF |
| Gate charge IC = 75A, VGE = 15 V,VCC =520V Tvj=25℃ | Q _G | | 130 | | nC |
| Turn-on delay time IC=75A, VCC=400 V Tvj=25℃ VGE=0/15 V, RG=10Ω Tvj=175℃ (inductive load) | td _(ON) | | 53 53 | | ns |
| Rise time IC=75A, VCC=400 V Tvj=25℃ VGE=0/15 V, RG=10Ω Tvj=175℃ (inductive load) | tr | | 132 128 | | ns |
| Turn-off delay time IC=75A, VCC=400 V Tvj=25℃ VGE=0/15 V, RG=10Ω Tvj=175℃ (inductive load) | td _(OFF) | | 162 181 | | ns |
| Fall time IC=75A, VCC=400 V Tvj=25℃ VGE=0/15 V, RG=10Ω Tvj=175℃ (inductive load) | tf | | 95 107 | | ns |

MD75S65JB0L

| Turn-on energy Tvj=25℃ IC=75A, VCC=400 V Tvj=25℃ VGE=0/15 V, RG=10Ω Tvj=175℃ (inductive load) Tvj=175℃ | E _(ON) | 3.3 4.8 | mJ |
|--|--------------------|------------|----|
| Turn-off energy loss per pulse IC=75A, VCC=400 V Tvj=25℃ VGE=0/15 V, RG=10Ω Tvj=175℃ (inductive load) | E _(OFF) | 2.2 2.7 | mJ |

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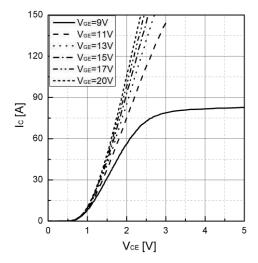


Figure 1. Typical output characteristics (Tvj=25°C)

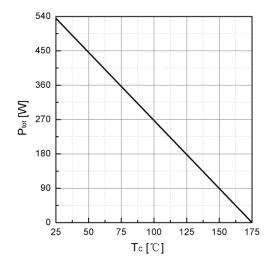


Figure 3. Power dissipation as a function of TC

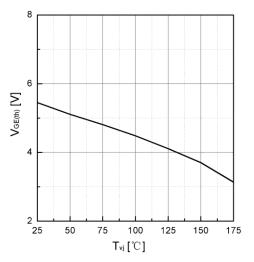


Figure 5. Typical VGE(th) as a function of Tvj ($I_C=1mA$)

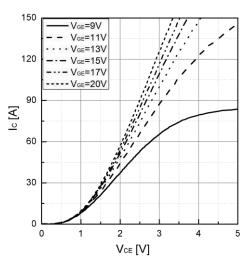


Figure 2. Typical output characteristics (Tvj=175°C)

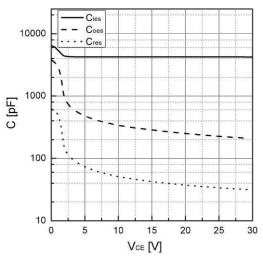


Figure 4. Typical capacitance as a function of VCE (f=1Mhz, VGE=0V)

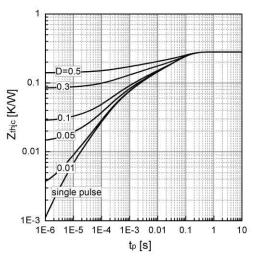


Figure 6. Transient thermal impedance of IGBT

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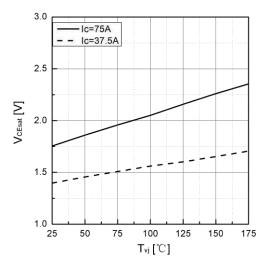


Figure 7. Typical VCEsat as a function of Tvj

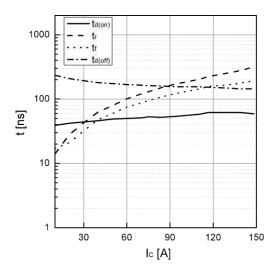


Figure 9. Typical switching times as a function of IC

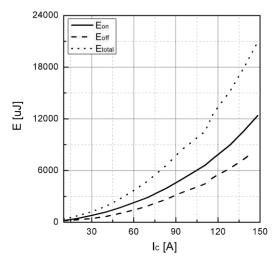


Figure 11. Typical switching energy losses as a function of IC

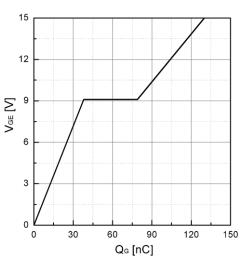


Figure 8. Typical Gate charge

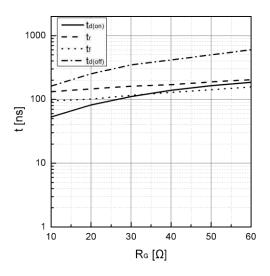


Figure 10. Typical switching times as a function of RG

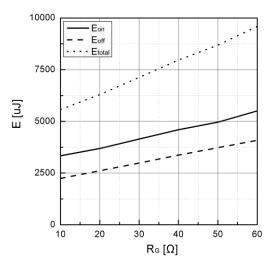
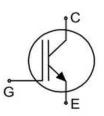
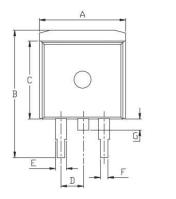


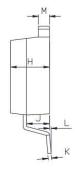
Figure 12. Typical switching energy losses as a function of RG

Circuit diagram



Package outlines : Dimensions in (mm)





| DIM | MILLIMETERS | | |
|-----|-------------|-------|--|
| DIN | MIN | MAX | |
| Α | 9.90 | 10.20 | |
| В | 14.70 | 15.80 | |
| С | 9.40 | 9.60 | |
| D | Typ. 2.54 | | |
| E | 1.20 | 1.40 | |
| F | 0.75 | 0.85 | |
| G | | 1.75 | |
| Н | 4.40 | 4.70 | |
| J | 2.30 | 2.70 | |
| K | 0.38 | 0.55 | |
| L | 0.00 | 0.25 | |
| М | 1.25 | 1.35 | |



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